

METAL SMALL-SIGNAL TRANSISTORS (continued)

Darlington Transistors

These transistors are characterized for very high gain and input impedance applications. Devices are of monolithic construction.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE}			I_C mA	$V_{CE(sat)}$ Volts Max	I_C mA	I_B mA
				Min	Max	@				
NPN										
TO-18	MM6427	40	300	5000			10	1.5	100	0.1
TO-39	BSS52	80	1000	2000	—		500	1.6	1000	4.0
	BSS51	60	1000	2000	—		500	1.6	1000	1.0
	BSS50	45	1000	2000	—		500	1.6	1000	4.0

High-Frequency Amplifiers/Oscillators

The transistors shown are designed for use as both oscillators and amplifiers at UHF and VHF frequencies. Devices are listed in decreasing order of $V_{(BR)CEO}$ with each line.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	h_{FE}		G_{pe} dB Min	NF		f MHz	f_T		C_{obo} pF Max
			Min	@ I_C mA		dB	@ MHz		Min	@ mA	
NPN											
TO-72	2N918†	15	20	3.0	15	6.0	60	600	4.0	1.7	
PNP											
TO-72	2N4261#	15	30	10	—	—	—	1600	10	2.5	

*JAN available

**JAN/JANTX available

†JAN/JANTX/JANTXV/JANS available

#JAN/JANTX/JANTXV available

High-Voltage/High-Current Amplifiers

The following table lists Motorola standard devices that have high Collector-Emitter Breakdown Voltage. Devices are listed in decreasing order of $V_{(BR)CEO}$ within each package type.

Package	Device Type	$V_{(BR)CEO}$ Volts Min	I_C mA Max	h_{FE}		$V_{CE(sat)}$ Volts Max	I_C mA	I_B mA	f_T		Comments
				Min	@ I_C mA				Min	@ mA	
NPN											
TO-18	BSS73	300	500	40	30	0.5	50	5	100	20	
	BSS72	250	500	40	30	0.5	50	5	100	20	
	BSS71	200	500	40	30	0.5	50	5	100	20	
	BC394	180	500	30	10	0.3	10	1.0	50	20	
TO-39	2N3439#	350	1000	40	20	0.5	50	4	15	10	Exists under CECC
	MM421	325	1000	25	30	5.0	30	3	15	10	
	BF259	300	100	25	30	1.0	30	6	110	30	
	BF258	250	100	25	30	1.0	30	6	110	30	
	2N3440#	250	1000	40	20	0.5	50	4	15	10	Exists under CECC
	BSS78	250	500	40	30	0.4	30	3	70	20	
	BF337	200	200	20	30	—	—	—	80	30	
BSS77	200	500	40	30	0.4	30	3	70	20		

JAN JANTX, JANTXV available